UNITED STATES PATENT AND TRADEMARK OFFICE **CERTIFICATE OF CORRECTION**

PATENT NO.

DATED

: 6,940,090 B2

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INVENTOR(S) : Saito et al.

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Title page, Item [54] and Column 1, lines 1-3,

Title, should read:

-- [54] A WIDEBAND GAP POWER SEMICONDUCTOR DEVICE HAVING A LOW ON-RESISTANCE AND HAVING A HIGH AVALANCHE CAPABILITY **USED FOR POWER CONTROL. --.**

Signed and Sealed this

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Thirteenth Day of December, 2005

JON W. DUDAS Director of the United States Patent and Trademark Office